Multi-gate quantum dots from armchair graphene nanoribbons

Jian Zhang,

Mickael Perrin, Oliver Braun, Gabriela Borin Barin, Rimah Darawish, Klaus Müllen, Pascal Ruffieux, Roman Fasel, Michel Calame

jian.zhang@empa.ch

Atomically precise graphene nanoribbons (GNRs) have attracted much interest from researchers worldwide, as they constitute an class of quantum-designed emerging materials, all tailored by controlling their width and edge structure during the chemical synthesis.[1-3] maior The challenges toward their exploitation in electronic applications include reliable contacting, complicated by their small size (<50 nm), and the preservation of their physical properties upon device integration. In recent years, the exploitation of GNR properties for electronic devices has focused on their integration into field-effecttransistor (FET) geometry.[4] However, such FET devices, due to the presence of a single gate, have limited electrostatic tunability. Here, we report on the device integration of armchair GNRs into a multi-gate FET geometry and a one-dimensional contact With geometry as well. the above geometries, we measured the quantum dot low-temperature. behavior at By demonstrating the preservation of the armchair GNRs' molecular levels upon device integration, as demonstrated by transport spectroscopy, our study provides a critical step forward in the realization of more exotic GNR-based quantum devices.

References

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Figures



Figure 1: GNR device and the transport measurement. (A) Artistic illustration of a multigate 9-AGNR quantum dot device. (B) A sketch of the GNRs grown parallel to the Au(788) terraces. (C) Coulomb diamonds in a multi-gate 9-AGNRs device at low temperature.